



#### **MMBTA55 / MMBTA56**

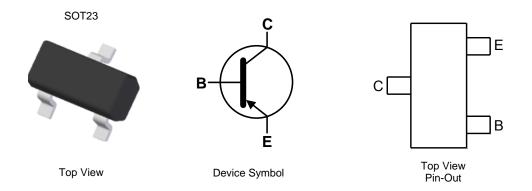
PNP SMALL SIGNAL TRANSISTOR IN SOT23

#### Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Complementary NPN Type: MMBTA05 / MMBTA06
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



### Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBTA55-7-F	AEC-Q101	K2G	7	8	3,000
MMBTA56-7-F	AEC-Q101	K2G	7	8	3,000
MMBTA56Q-7-F	Automotive	K2G	7	8	3,000
MMBTA56Q-13-F	Automotive	K2G	13	8	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

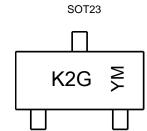
 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

 Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



K2G = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Balo Codo Hoy												
Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	С	D	E	F	G	Н		J	K	L	М	Ν
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	MMBTA55	MMBTA56	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-60	-80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	-80	V
Emitter-Base Voltage	V <sub>EBO</sub>	-4	.0	V
Collector Current - Continuous	Ι <sub>C</sub>	-5	00	mA

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Dower Dissinction	(Note 6)	D	310	mW
Power Dissipation	(Note 7)	P <sub>D</sub>	350	TIVV
Thermal Desistance, Junction to Ambient	(Note 6)		403	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>θJA</sub>	357	C/W
Thermal Resistance, Junction to Leads (Note 8)		R <sub>θJL</sub>	350	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 to +150	°C	

# ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

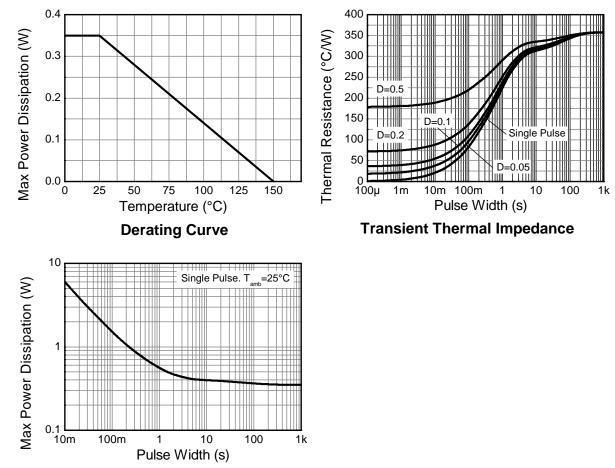
Notes: 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air

conditions whilst operating in a steady-state.

Same as Note 6, except the device is mounted on 15 mm x 15mm 1oz copper.
Thermal resistance from junction to solder-point (at the end of the leads).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# Thermal Characteristics and Derating Information



**Pulse Power Dissipation** 

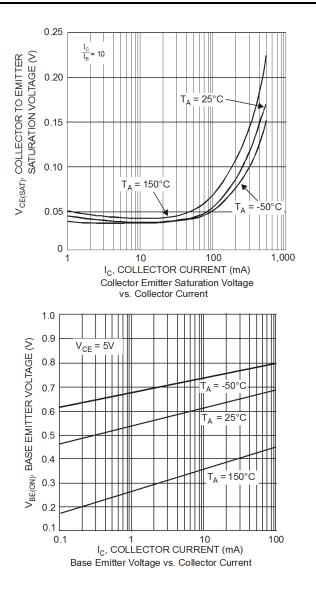
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

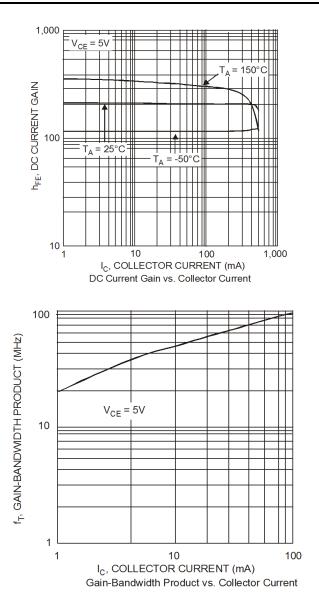
Characteristic			Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)				•		÷
Collector-Base Breakdown Voltage	MMBTA55 MMBTA56	BV <sub>CBO</sub>	-60 -80	—	V	$I_{\rm C} = -100 \mu {\rm A}, \ I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	MMBTA55 MMBTA56	BV <sub>CEO</sub>	-60 -80	—	V	$I_{\rm C} = -1.0 {\rm mA}, \ I_{\rm B} = 0$
Emitter-Base Breakdown Voltage		BV <sub>EBO</sub>	-5.0	-4.0	_	$I_{\rm E} = -100 \mu A$ , $I_{\rm C} = 0$
Collector Cut-Off Current	MMBTA55 MMBTA56	I <sub>CBO</sub>	_	-100	nA	$V_{CB} = -60V, I_E = 0$ $V_{CB} = -80V, I_E = 0$
Collector Cut-Off Current		ICEX	—	-100	nA	$V_{CE} = -60V, I_{BO} = 0V$ $V_{CE} = -80V, I_{BO} = 0V$
ON CHARACTERISTICS (Note 10)						-
DC Current Gain		h <sub>FE</sub>	100	_	—	$I_{C} = -10mA, V_{CE} = -1.0V$ $I_{C} = -100mA, V_{CE} = -1.0V$
Collector-Emitter Saturation Voltage		V <sub>CE(SAT)</sub>	_	-0.25	V	$I_{\rm C} = -100 {\rm mA}, I_{\rm B} = -10 {\rm mA}$
Base-Emitter Saturation Voltage	VBE(SAT)		-1.2	V	I <sub>C</sub> = -100mA, V <sub>CE</sub> = -1.0V	
SMALL SIGNAL CHARACTERISTICS				•	•	÷
Current Gain-Bandwidth Product		f⊤	50	_	MHz	$V_{CE} = -1.0V, I_C = -100mA, f = 100MHz$

Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

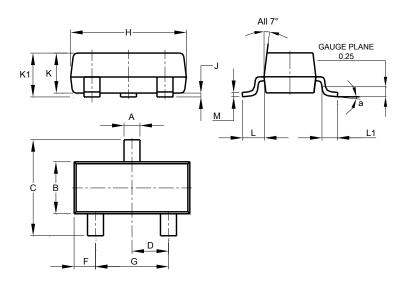






# **Package Outline Dimensions**

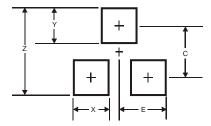
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
К	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а		8°				
All	Dimens	ions in	mm			

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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